

**AMENDMENTS TO THE CLAIMS**

Please cancel claims 1-7 and 15-20 without prejudice or disclaimer of their underlying subject matter.

1-20. (Canceled)

Please add the following new claims.

21. (New) An exposure method comprising the steps of:

providing a V-line reflective mask, a mask pattern for said V-line reflective mask consisting of V-line pattern forming elements;

providing an H-line reflective mask, a mask pattern for said H-line reflective mask consisting of H-line pattern forming elements;

irradiating a light onto one of said V-line and H-line reflective masks, said light reflected from said one of said V-line and H-line reflective masks being projected onto a wafer;

rotating said wafer and another of said V-line and H-line reflective masks; and

irradiating said light onto said another of said V-line and H-line reflective masks, said light reflected from said another of said V-line and H-line reflective masks being projected onto said wafer.

22. (New) The exposure method as cited in Claim 21, wherein the step of irradiating said light onto said another of said V-line and H-line reflective masks is performed after the step of rotating said wafer and another of said V-line and H-line reflective masks.

23. (New) The exposure method as cited in Claim 21, wherein the step of rotating said wafer and another of said V-line and H-line reflective masks includes rotating said wafer and another of said V-line and H-line reflective masks by approximately 90 degrees.

24. (New) The mask fabrication method as cited in Claim 21, wherein said mask pattern for said V-line reflective mask consists only of said V-line pattern forming elements.

25. (New) The mask fabrication method as cited in Claim 21, wherein said mask pattern for said H-line reflective mask consists only of said H-line pattern forming elements.

26. (New) The exposure method as cited in Claim 21, wherein a projection of said of V-line pattern forming elements is adapted to extend onto said wafer in a first direction.

27. (New) The exposure method as cited in Claim 26, wherein a projection of said of H-line pattern forming elements is adapted to extend onto said wafer in a direction other than said first direction.

28. (New) The exposure method as cited in Claim 21, wherein said light is from the group consisting of a charged particle beam, an x-ray, an extreme ultra violet ray, an ultra violet ray, and a visible light.

29. (New) The exposure method as cited in Claim 28, wherein said charged particle beam is one of an electron beam and an ion beam.

30. (New) A fabrication method of a semiconductor device comprising the steps of:  
acquiring input data, said input data corresponding to an LSI pattern to be formed on a wafer;

dividing said input data into V-line data and H-line data, said V-line data corresponding to V-line pattern forming elements and said H-line data corresponding to H-line pattern forming elements; and

performing the exposure method of claim 21.